



Material Composition Declaration

EPC2366

Company Name	Efficient Power Conversion (EPC)	Issue Date:	2026/3/13
Contact Name:	Yanping Ma	Contact Title:	VP Quality
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Part Weight:	18.7 mg	Type of Product:	eGaN FET in FCQFN package

Construction Element	Substance	CAS No. If Applicable	Weight	Mass	Sum (%)	Mass
			(mg)	(%)		(ppm)
Chip	Silicon	7440-21-3	4.0874	21.8439	22.7523	218439
	Silicon oxide	7631-86-9	0.0185	0.0988		988
	Silicon nitride	12033-89-5	0.0155	0.0830		830
	Gallium nitride	25617-97-4	0.0215	0.1147		1147
	Aluminum	7429-90-5	0.0194	0.1038		1038
	Aluminum nitride	24304-00-5	0.0036	0.0195		195
	Titanium	7440-32-6	0.0335	0.1790		1790
	Titanium nitride	25583-20-4	0.0032	0.0172		172
	Copper	7440-50-8	0.0003	0.0017		17
	Tungsten	7440-33-7	0.0049	0.0259		259
	Polyimide		0.0495	0.2648		2648
Under Bump Metal	Titanium	7440-32-6	0.0006	0.0034	0.0377	34
	Copper	7440-50-8	0.0064	0.0343		343
Internal Solder Bump	Copper	7440-50-8	0.7953	4.2503	5.5654	42503
	Nickel	7440-02-0	0.0383	0.2045		2045
	Tin	7440-31-5	0.2041	1.0906		10906
	Silver	7440-22-4	0.0037	0.0200		200
Package	Copper	7440-50-8	7.6381	40.8197	70.9397	408197
	Mold Compound		5.6360	30.1199		301199
External pins Coating	Nickel	7440-02-0	0.1297	0.6933	0.7050	6933
	Palladium	7440-05-3	0.0012	0.0063		63
	Potassium Gold Cyanide	13967-50-5	0.0010	0.0053		53
Sum in total:			18.71	100.00	100.00	1000000

Note:

The substance content disclosed herewith is approximate and is based on engineering calculation. Statements are based on our present knowledge and may subject to change at any time due to technical requirements and development. EPC may update this document without notification. Statement may not include information regarding the minute quantities of dopant and metal materials in the electrical devices contained within the finished product.